## Atomically sharp domain walls in epitaxial CuMnAs

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High quality thin films of tetragonal CuMnAs [1] grown by molecular beam epitaxy, were recently implemented in novel Spintronic devices. These rely on different phenomena, as are for example Néel vector reorientation via spin-orbit coupling [2] or thermal Quenching into high resistivity states [3].

We will present the results of our transmission electron microscopy measurements of the magnetic structure of epitaxial CuMnAs thin films on the atomic scale to demonstrate the existence of atomically sharp antiferromagnetic domain walls [4]. These results do not only help us explain the physical mechanisms behind interesting functionalities of CuMnAs devices [5], but also to get a better understanding of the crystalline/magnetic structure interplay in antiferromagnets.

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